

# MA3XD17

## Silicon epitaxial planar type

For rectification

For protection against reverse current

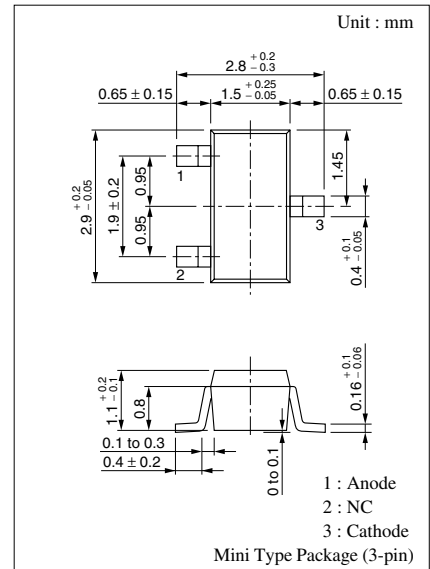
### ■ Features

- Mini type 3-pin package
- High breakdown voltage  $V_R = 100$  V

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

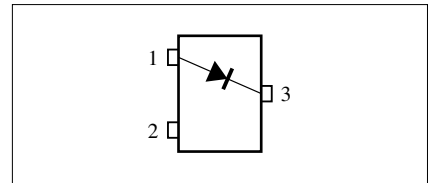
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	100	V
Peak reverse voltage	$V_{RM}$	100	V
Non-repetitive peak forward surge current*	$I_{FSM}$	1.5	A
Average forward current	$I_{F(AV)}$	300	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \* : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)



Marking Symbol: M5K

Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 100$ V			200	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 300$ mA		0.50	0.58	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		100		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100$ mA $I_{Tr} = 0.1 \cdot I_R$ , $R_L = 100 \Omega$		7		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

1. Rated input/output frequency: 250 MHz
3. \*:  $t_{rr}$  measuring circuit

